

AMENDMENTS TO THE SPECIFICATION

Page 7, replace paragraph commencing at line 11 with the following amended paragraph:

In content of the layers 209a and 209b can be expressed as Equation (1) below.

~~2% (1st InGaN layer) ≤ In/InGa ≤ 3% (2nd InGaN layer) (1)~~

In/InGa in 1st InGaN layer ≤ 2 %;

In/InGa in 2nd InGaN layer ≤ 3%; and (1)

In/InGa in 1st InGaN layer ≤ In/InGa in 2nd InGaN layer

Page 8, replace paragraph commencing at line 34 with the following amended paragraph:

It can be seen from Table 1 that the inventive light emitting device equipped with the InGaN/InGaN multi-layer 209 can normally operate even when an about-20-time higher ~~reverse~~ reverse voltage is applied thereto.